

CLAIMS LISTING

- 1.(original) A process for preparing a capacitor comprising:
fabricating an aluminum plate;
pre-hydrating said aluminium plate;
contacting said plate with an anodizing solution comprising
glycerine, about 0.1 to about 2.0%, by weight, water
and about 0.01 to about 0.5%, by weight,
orthophosphate;
applying a voltage to said aluminum plate of at least about
220 volts.
- 2.(original) The process for preparing a capacitor of claim 1
further comprising the step of:
etching said aluminum plate prior to said pre-hydrating of
said aluminum plate.
- 3.(original) The process for preparing a capacitor of claim 1
wherein said voltage is applied in increasing increments
with an age time between each said increment.
- 4.(original) The process for preparing a capacitor of claim 3
wherein said increments are less than about 75 volts.
- 5.(original) The process for preparing a capacitor of claim 4
wherein said increments are at least about 20 V to no more
than about 50 V.

- 6.(original) The process for preparing a capacitor of claim 5 wherein said age time is sufficient for the current to decrease to from about 1 to about 50% of an initial current.
- 7.(original) The process for preparing a capacitor of claim 6 wherein said age time is sufficient for the current to decrease to from about 10 to about 30% of said initial current.
- 8.(original) The process for preparing a capacitor of claim 7 wherein said age time is sufficient for the current to decrease to about 20% of said initial current.
- 9.(original) The process for preparing a capacitor of claim 1 wherein said anodizing solution is at a temperature of about 25°C to about 125°C.
- 10.(original) The process for preparing a capacitor of claim 9 wherein said anodizing solution is at a temperature of about 80°C to about 105°C.
- 11.(original) The process for forming a capacitor of claim 1 wherein said anodizing solution comprises about 0.01 to about 0.1%, by weight, soluble orthophosphate.
- 12.(original) The process for forming a capacitor of claim 1 wherein said soluble orthophosphate is selected from a

group consisting of ammonium phosphate, alkali metal phosphate, amine phosphate or mixtures thereof.

13.(original) The process for forming a capacitor of claim 1 wherein said soluble orthophosphate is selected from a group consisting of mono-sodium phosphate, di-potassium phosphate, and sodium potassium phosphate.

14.(original) The process for forming a capacitor of claim 1 wherein said soluble orthophosphate is selected from a group consisting of mono-ammonium phosphate and di-ammonium phosphate.

15.(original) The process for forming a capacitor of claim 1 wherein said anodising solution comprises about 0.1 to about 1%, by weight, water.

16-18.(cancelled)

19.(original) A process for preparing a capacitor comprising:

fabricating an aluminum plate;

pre-hydrating said aluminium plate;

contacting said plate with an anodizing solution comprising

glycerine, about 0.1 to about 2.0%, by weight, water

and about 0.01 to about 0.5%, by weight,

orthophosphate;

applying a voltage to said aluminum plate and determining

an initial current;

maintaining said first voltage until a first measured
current is no more than 50% of said initial current;
increasing said voltage and redetermining said initial
current;

maintaining said increased voltage until a second measured
current is no more than about 50% of said redetermined
initial current, and
continuing said increasing said voltage and said maintaining
said increased voltage until a final voltage is
achieved.

20.(original) The process for preparing a capacitor of claim 19
further comprising the step of:

etching said aluminum plate prior to said pre-
hydrating of said aluminum plate.

21.(original) The process for preparing a capacitor of claim 19
wherein said final voltage is above 220 volts.

22.(original) The process for preparing a capacitor of claim 19
wherein said voltage is increased by no more than about 75
volts.

23.(original) The process for preparing a capacitor of claim 22
wherein said voltage is increased by at least about 20 V to
no more than about 50 V.

- 24.(original) The process for preparing a capacitor of claim 23 wherein said first measured current or said second measured current is from about 1 to about 50% of said initial current.
- 25.(original) The process for preparing a capacitor of claim 24 wherein said first measured current or said second measured current is from about 10 to about 30% of said initial current.
- 26.(original) The process for preparing a capacitor of claim 25 wherein said first measured current or said second measured current is about 20% of said initial current.
- 27.(original) The process for preparing a capacitor of claim 19 wherein said anodizing solution is at a temperature of about 25°C to about 125°C.
- 28.(original) The process for preparing a capacitor of claim 27 wherein said anodizing solution is at a temperature of about 80°C to about 105°C.
- 29.(original) The process for forming a capacitor of claim 19 wherein said anodizing solution comprises about 0.01 to about 0.1%, by weight, soluble orthophosphate.
- 30.(original) The process for forming a capacitor of claim 19 wherein said soluble orthophosphate is selected from a

group consisting of ammonium phosphate, alkali metal phosphate, amine phosphate and mixtures thereof.

31.(original) The process for forming a capacitor of claim 19 wherein said soluble orthophosphate is selected from a group consisting of mono-sodium phosphate, di-potassium phosphate, and sodium potassium phosphate.

32.(original) The process for forming a capacitor of claim 19 wherein said soluble orthophosphate is selected from a group consisting of mono-ammonium phosphate and di-ammonium phosphate.

33-36.(cancelled)